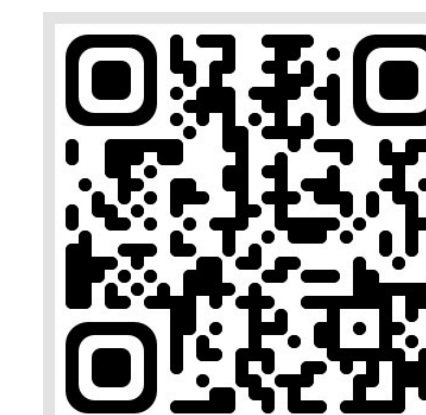


Optimization of Transformer Design Parameters of a 20 kW SiC-Based Dual-Active Bridge Converter for Enhanced Efficiency

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OBJECTIVES

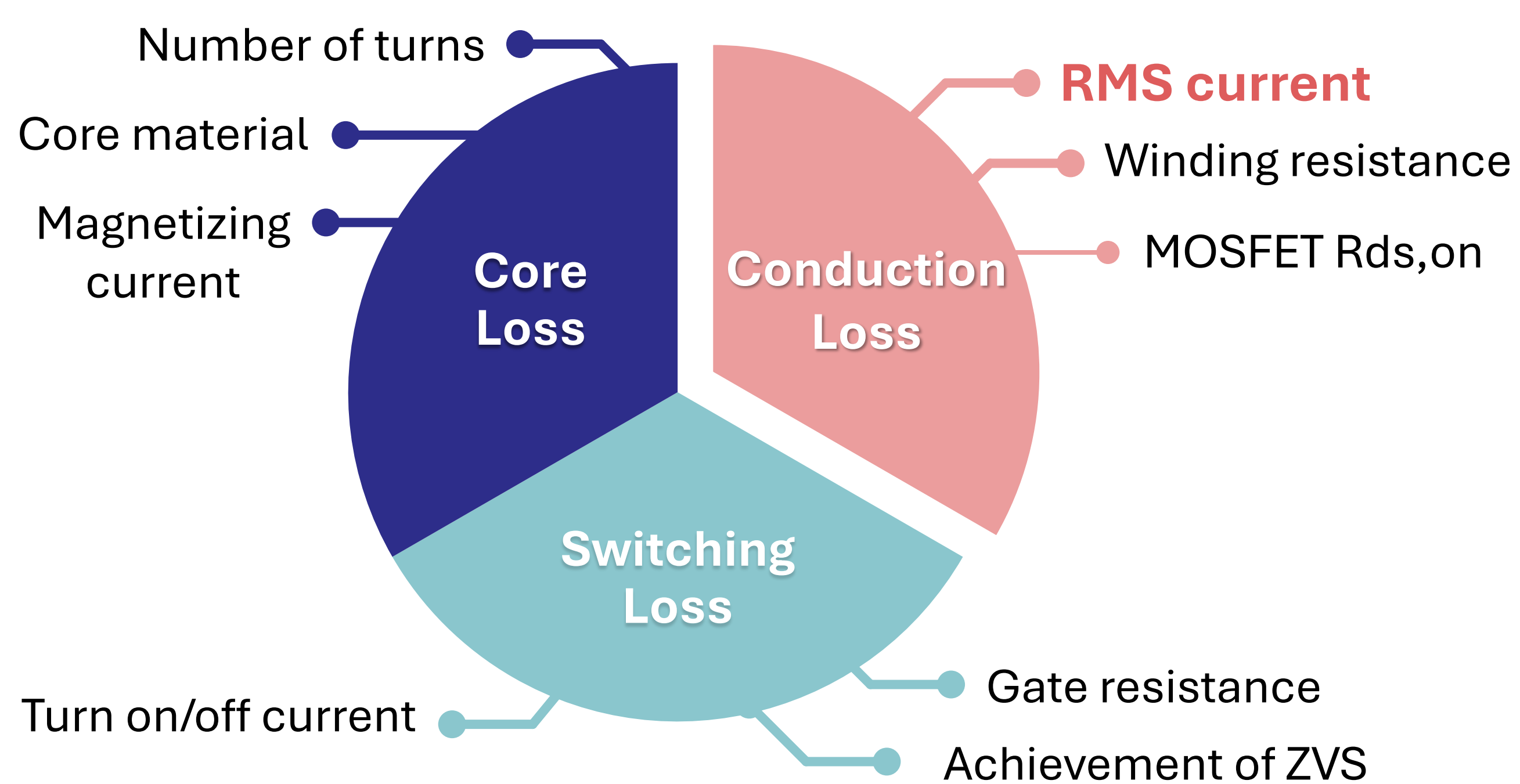
- To derive optimal leakage inductance and turns ratio of dual-active bridge (DAB) for high efficiency

KEY ISSUES

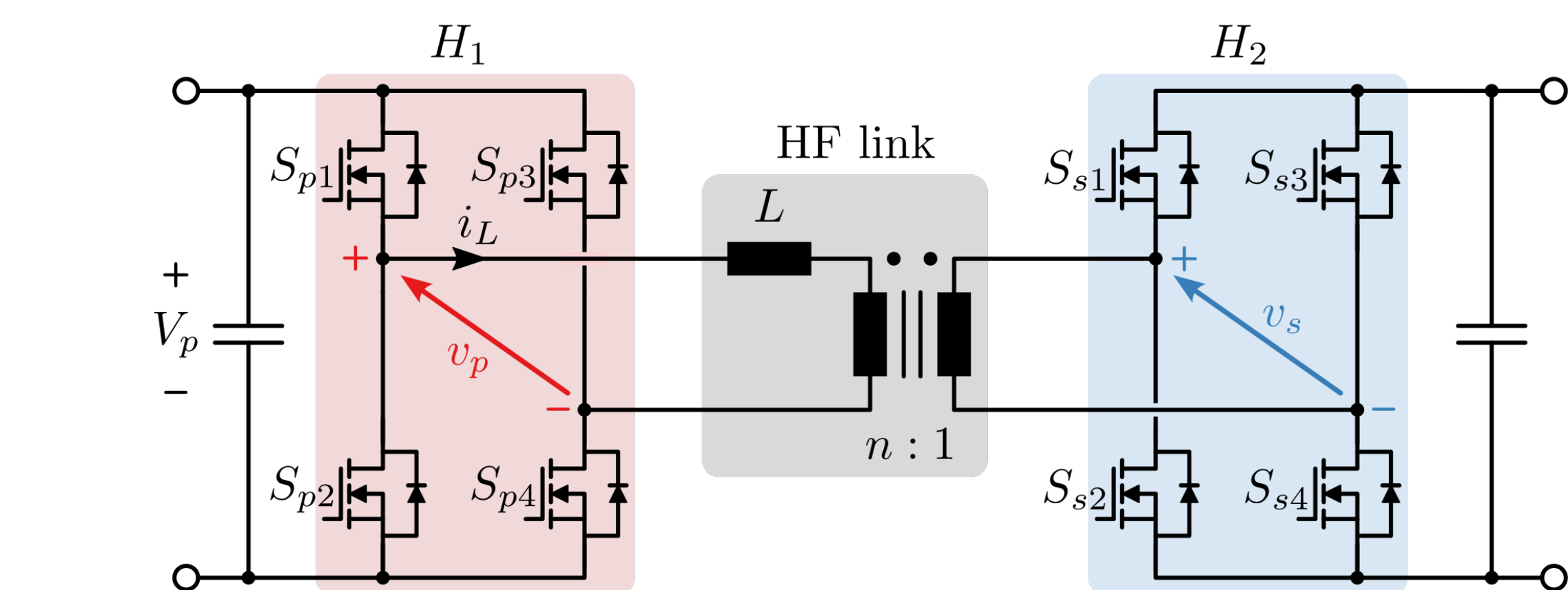
- Selecting triple-phase-shift (TPS) modulation scheme
- Minimization of conduction and switching losses

1 Introduction

Loss Components of DAB Converters



Minimization of Conduction Loss



Modulation Parameters (D_p, D_s, D_ϕ)

- Single-phase-shift
- Triple-phase shift
 - ✓ ZVS constraints
 - ✓ RMS current minimization

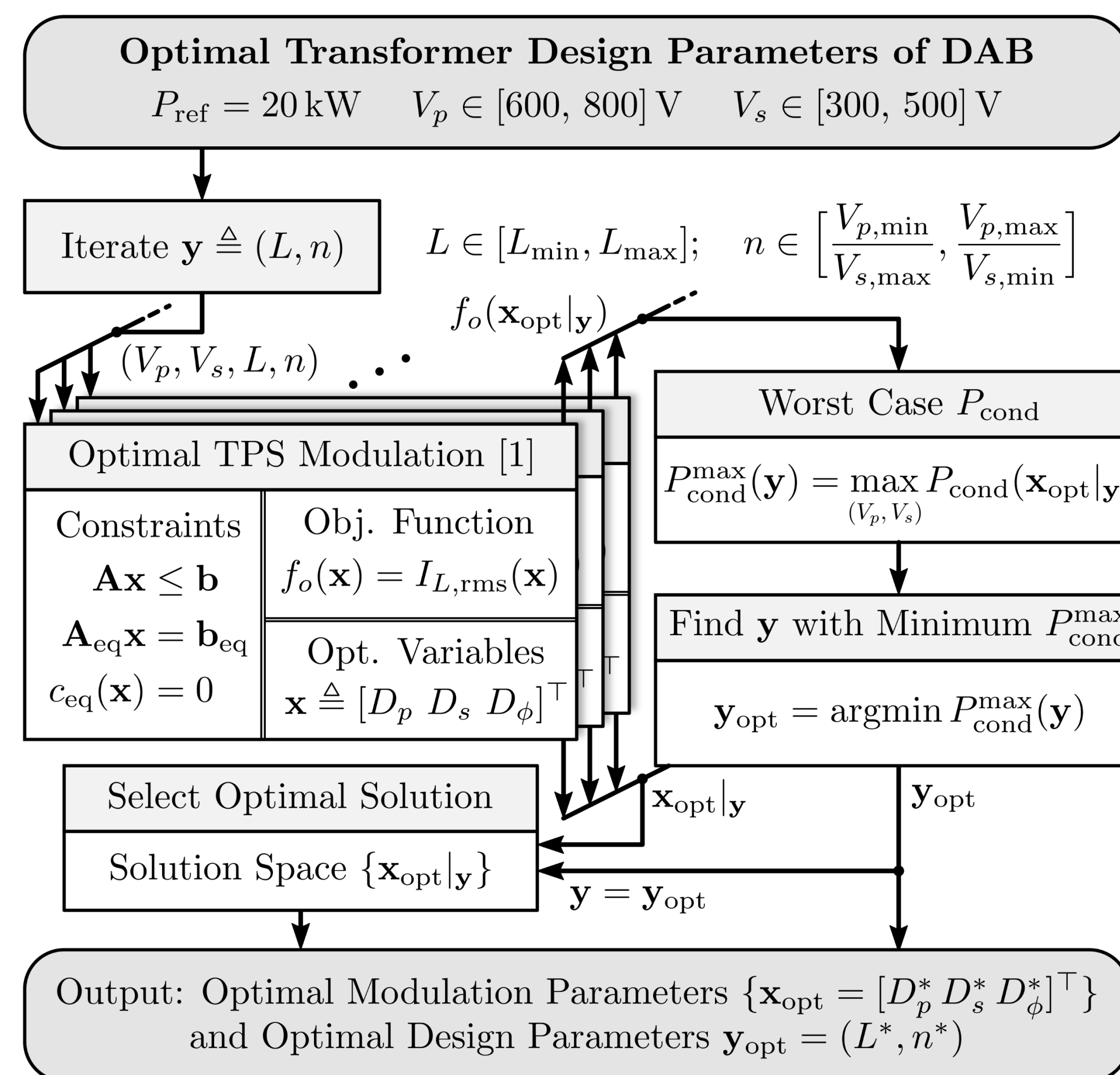
Transformer Parameters (L, n)

- Leakage inductance L , turns ratio n
- Optimization objective
 - ✓ Peak current minimization
 - ✓ Conduction loss minimization

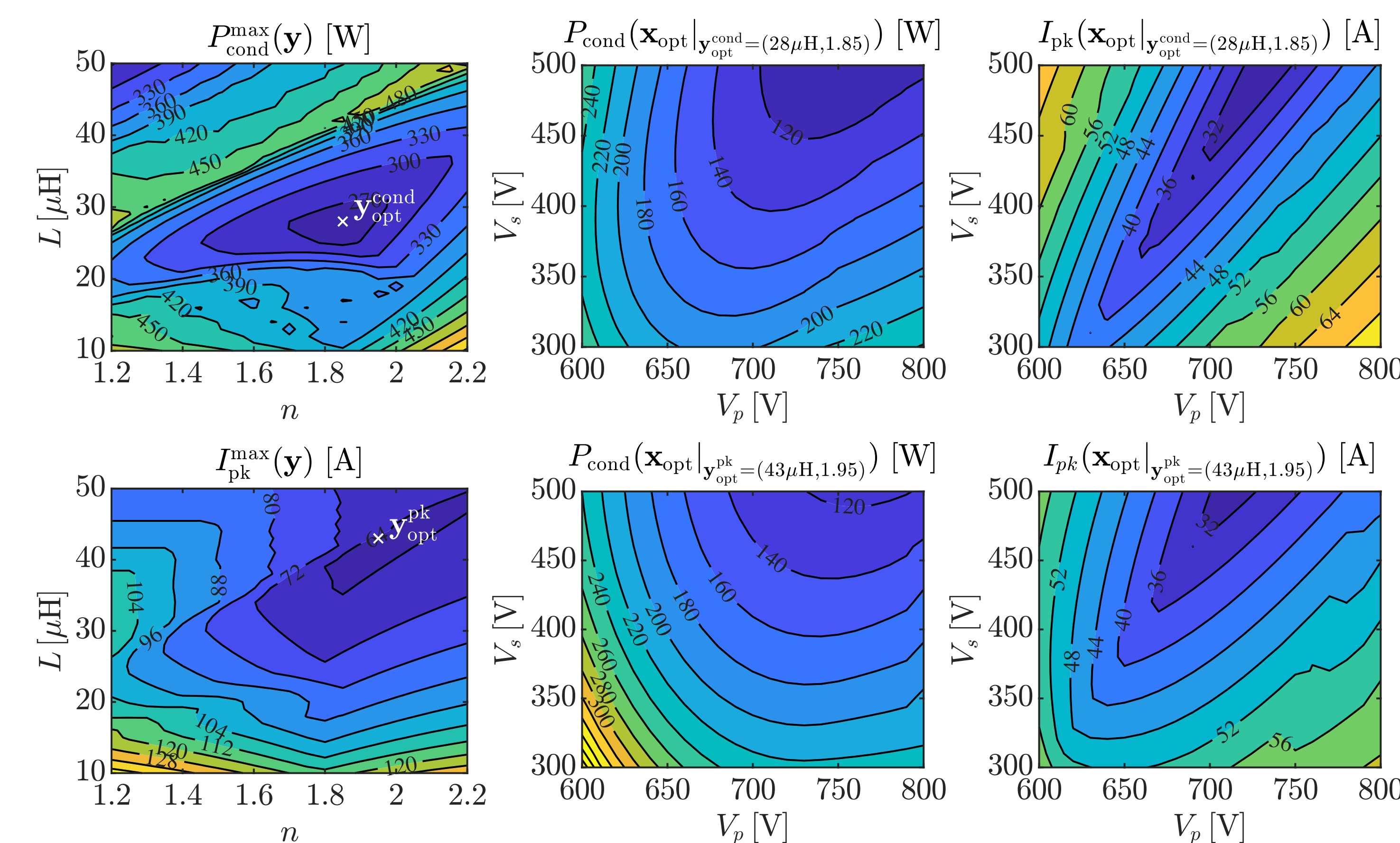
Find optimal (L^*, n^*) for Conduction Loss minimization using ZVS-enhanced TPS modulation [1]

2 Proposed Optimal Transformer Parameters

Optimization Procedure



Transformer Parameters for Minimum Conduction Loss



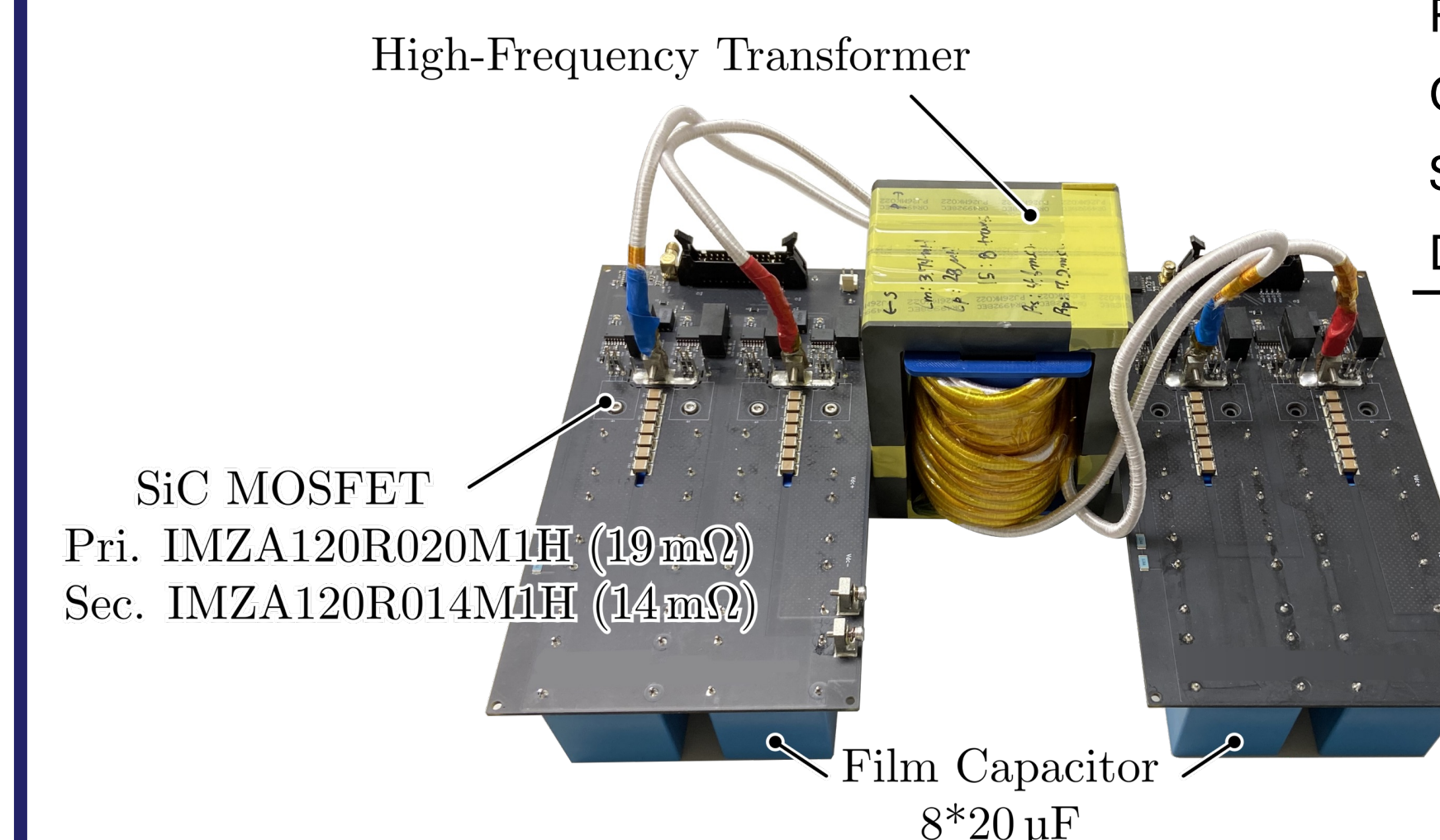
Design Parameters of High-Frequency Transformers

	Objective function	L	n (number of turns)
Proposed	Conduction loss	Cal.	28 μ H
		Exp.	28 μ H
Comparison [2]	Peak current	Cal.	43 μ H
		Exp.	41 μ H

3 Experimental Verification

Experimental Setup

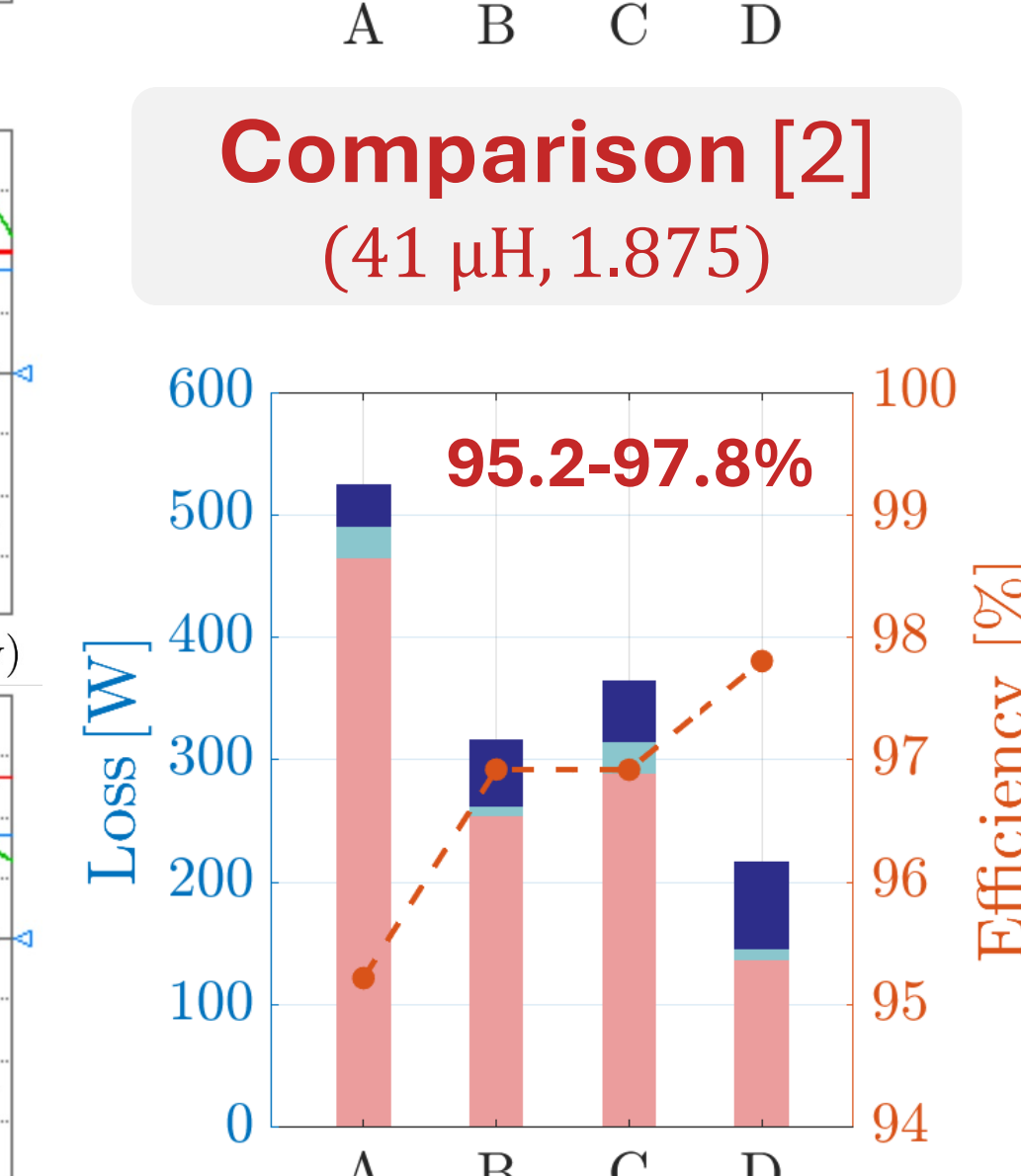
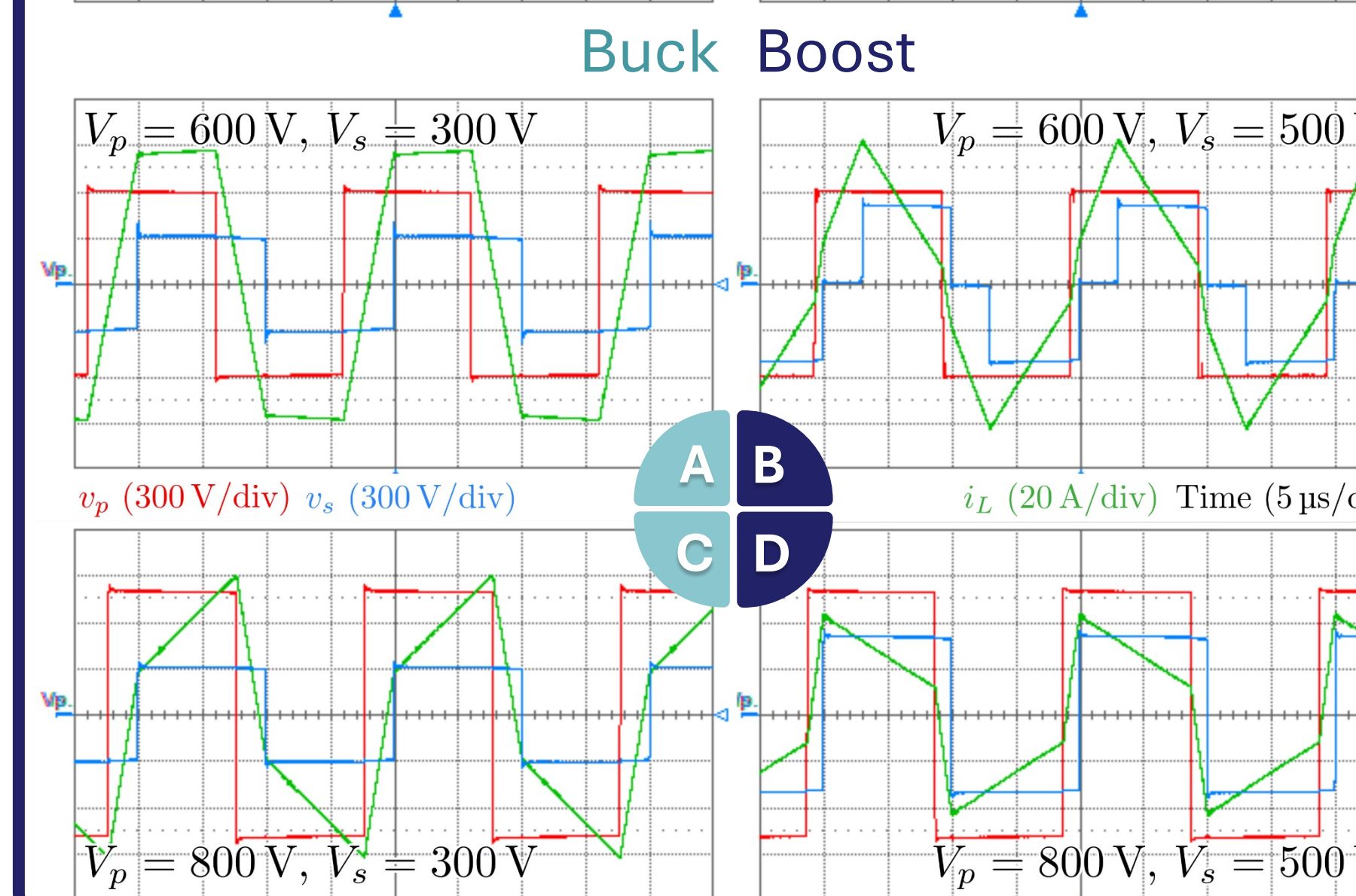
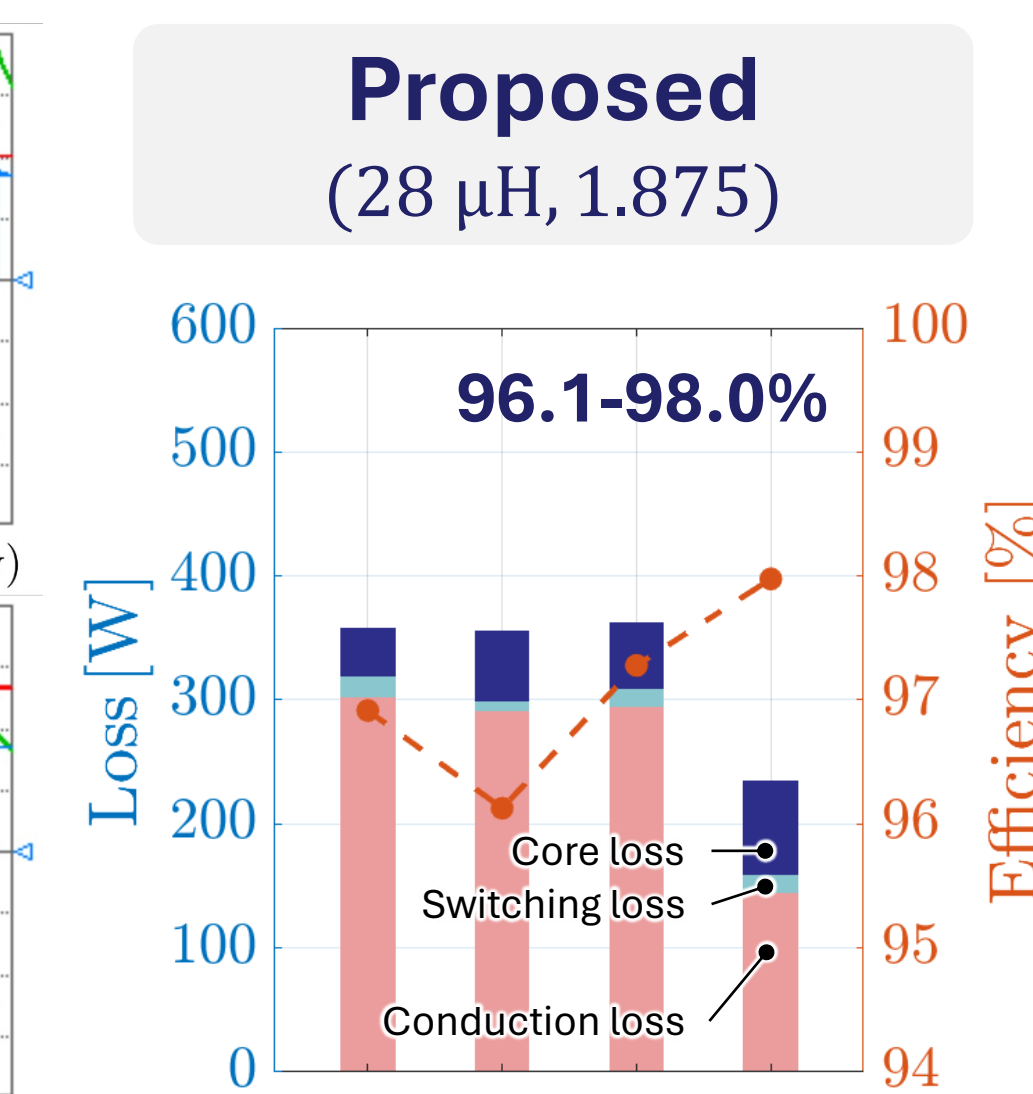
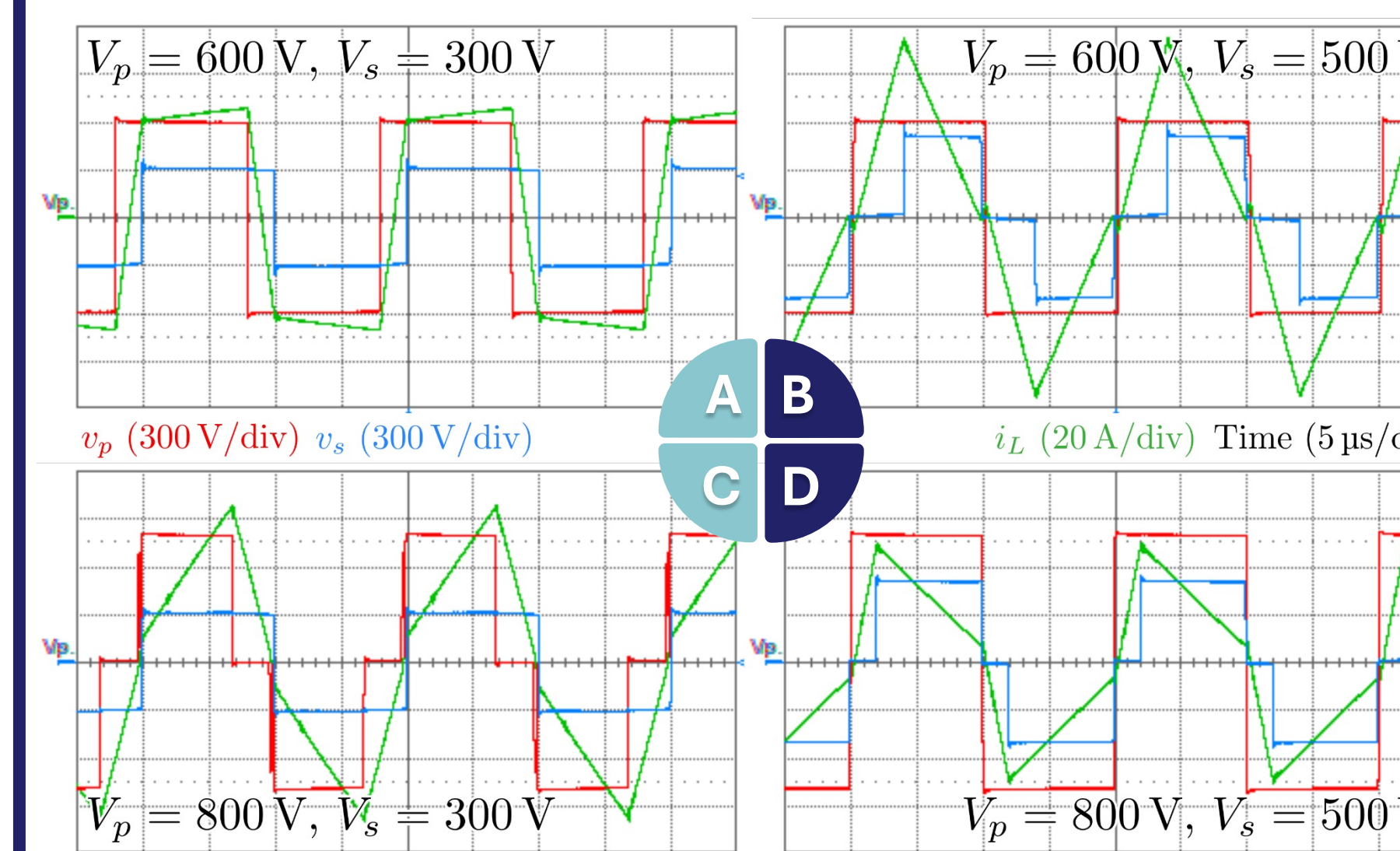
Hardware Specifications



Parameter	Value
Input voltage V_p	600 V-800 V
Output voltage V_s	300 V-500 V
Rated power P_{rated}	20 kW
Controller	TMS320F28377D
Switching frequency f_s	50 kHz
Dead time T_{dt}	300 ns

- Leakage inductance L 28 μ H
- Turns ratio n 1.875
- Pri. 15 turns (7.3 m Ω)
- Sec. 8 turns (4 m Ω)
- Litz wire 0.12mm*1000 strands
- Core 0R49928EC*6EA
- Magnetizing inductance L_m 3.74 mH

Measured Efficiency and Estimated Loss Breakdown



4 Conclusion & Future Works

- Proposed optimal parameters improve efficiency at rated load across wide voltage range with optimal TPS modulation
- Objective function can be refined to reflect accurate loss characteristics of MOSFETs and transformers

[1] G. Park, H. Kim, B.-G. Cho, and S. Cui, "ZVS-Enhanced and RMS-Current-Minimized Optimal Modulation Scheme of Dual-Active Bridge Converter with Comprehensive ZVS Analysis," unpublished.
[2] H. Zhang, Z. Liu, Y. Song, P. Han, and J. Liu, "A Current-Stress-Optimized Design Method for Dual Active Bridge Converters With Improved V S Capability Under Wide Output Voltage Conditions," IEEE Transactions on Industrial Electronics, vol. 71, no. 6, pp. 5807-5817, Jun. 2024.